

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)
2. (Currently Amended) A method of manufacturing a three-dimensional stacking type semiconductor ~~device using the semiconductor device as defined in claim 1, the method device,~~ comprising:

forming an electrode layer on each of a plurality of substrates, the electrode layer having a plurality of conductive layers with an insulating layer interposed between at least two adjacent conductive layers of the plurality of conductive layers, each of the at least two adjacent conductive layers being lower than an uppermost conductive layer and having a through-hole formed therein, the through-hole being filled with an insulating material;

~~a semiconductor device formation step which includes an electrode layer through hole formation step of forming a hole in the uppermost conductive layer coaxially with the through-hole in each of the at least two adjacent conductive layers lower than the uppermost conductive layer, and forming an electrode layer through-hole in the electrode layer by etching the insulating material, a step of material;~~

forming a substrate through-hole connected with the electrode layer through-hole in the substrate, and a step of each of the substrates;

filling the electrode layer through-hole and the substrate through-hole in each of the substrates with a conductive member; and

~~a semiconductor device stacking step of stacking a plurality of the semiconductor devices~~stacking the substrates by using ~~at the~~ conductive member of each of the ~~semiconductor devices~~substrates.

- 3-4. (Canceled)